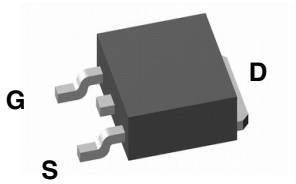
N-Channel PowerTrench® MOSFET

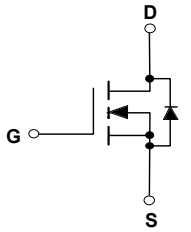
60V, 58A, 12mΩ

Features

- $R_{DS(ON)}$ = 12 mΩ @ V_{GS} = 10 V
- $R_{DS(ON)}$ = 16 mΩ @ V_{GS} = 4.5 V



TO-252



ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	58	A
	T_C = 100 °C		48[a]	
Pulsed Drain Current		I_{DM}	100	
Continuous Source Current (Diode Conduction)		I_S	50[a]	
Avalanche Current		I_{AS}	50	
Single Avalanche Energy (Duty Cycle≤ 1 %)	L = 0.1 mH	E_{AS}	125	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	136	W
	T_A = 25 °C		3[b], 8.3[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t ≤ 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.[a]	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	123			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	60			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.012		Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125 °C		0.016		
		V_{GS} = 10 V, I_D = 20 A, T_J = 175 °C		0.020		
		V_{GS} = 4.5 V, I_D = 15 A		0.013		
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		60		S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2650		pF
Output Capacitance	C_{oss}			470		
Reverse Transfer Capacitance	C_{rss}			225		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 50 A		47	70	nC
Gate-Source Charge[c]	Q_{gs}			10		
Gate-Drain Charge[c]	Q_{gd}			12		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.6 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 2.5 Ω		10	20	ns
Rise Time[c]	t_r			15	25	
Turn-Off Delay Time[c]	$t_{d(off)}$			35	50	
Fall Time[c]	t_f			20	30	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				60	A
Diode Forward Voltage	V_{SD}	I_F = 20 A, V_{GS} = 0 V		11.5V		
Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/µs		45	100	ns

Notes:

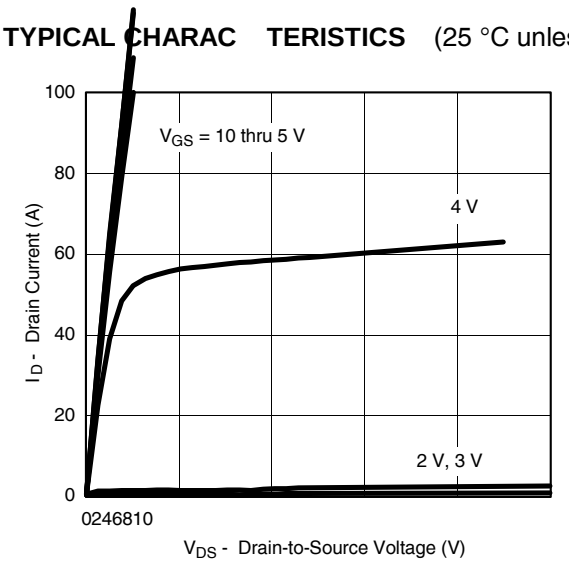
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

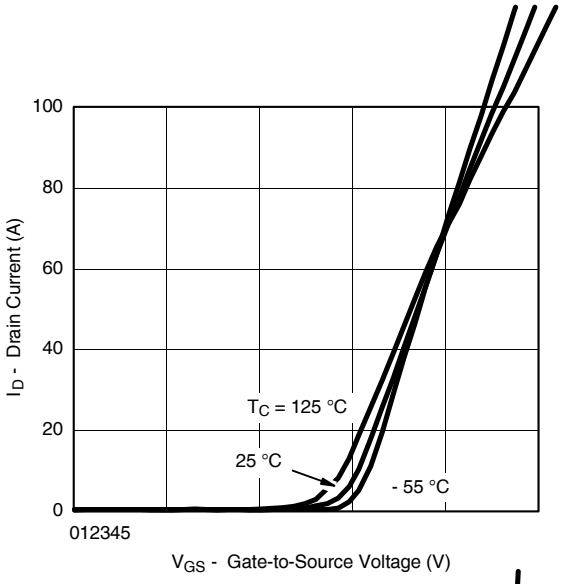
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

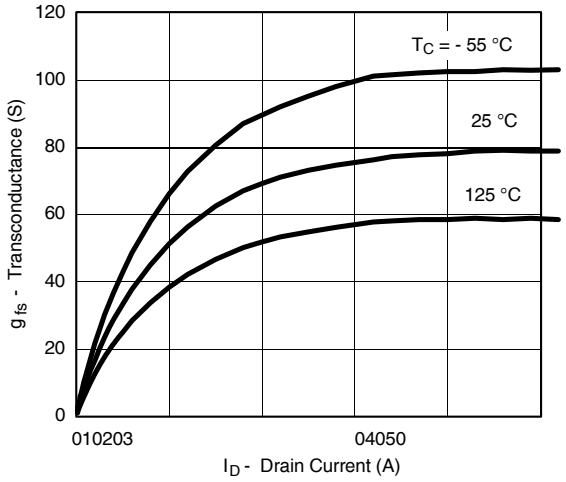
TYPICAL CHARAC TERISTICS (25 °C unless noted)



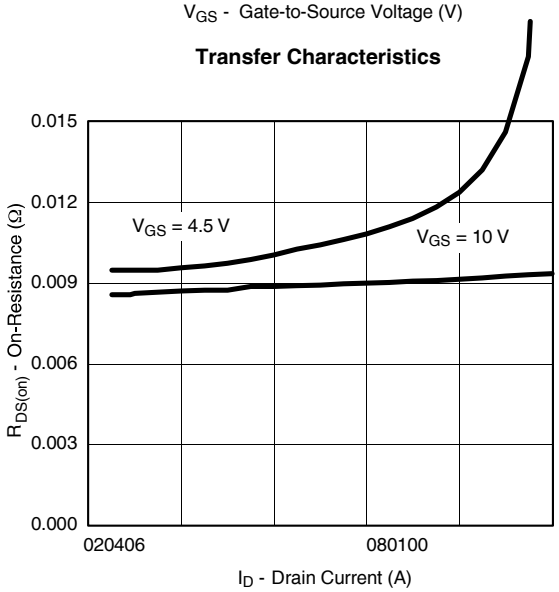
Output Characteristics



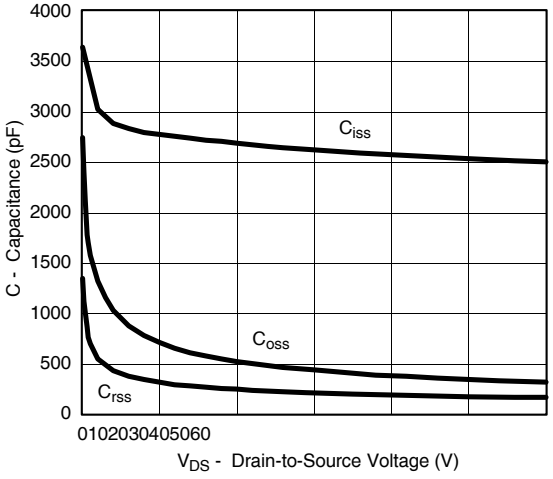
Transfer Characteristics



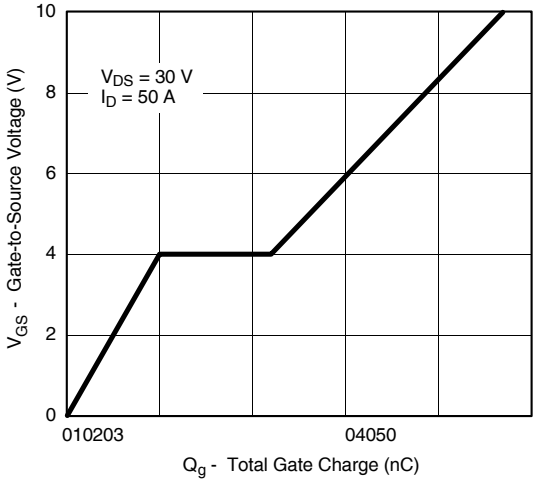
Transconductance



On-Resistance vs. Drain Current

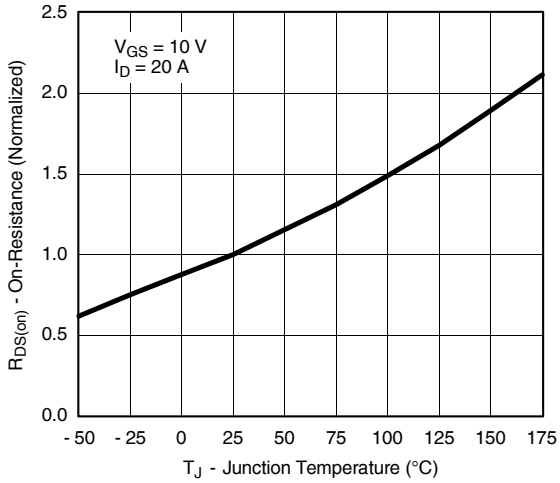


Capacitance

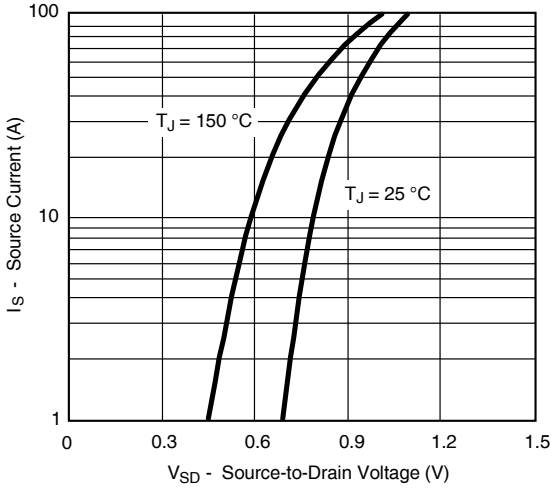


Gate Charge

TYPICAL CHARACTERISTICS (25 °C unless noted)

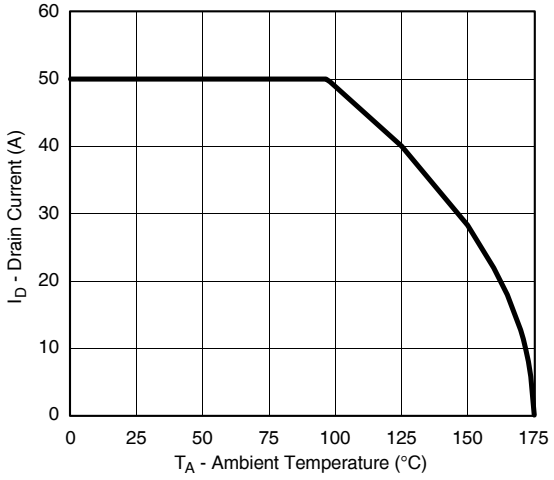


On-Resistance vs. Junction Temperature

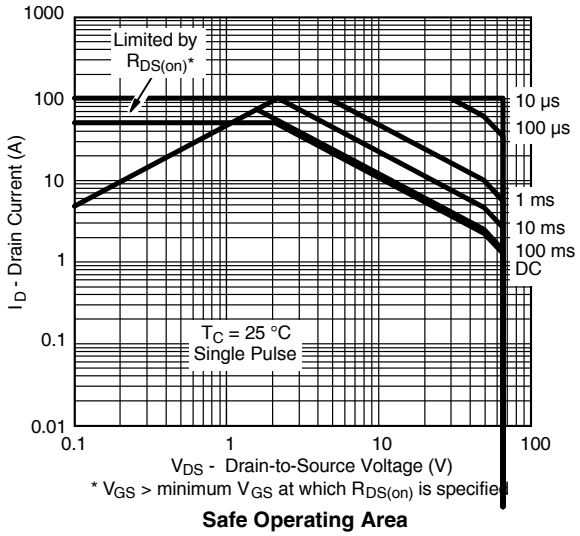


Source-Drain Diode Forward Voltage

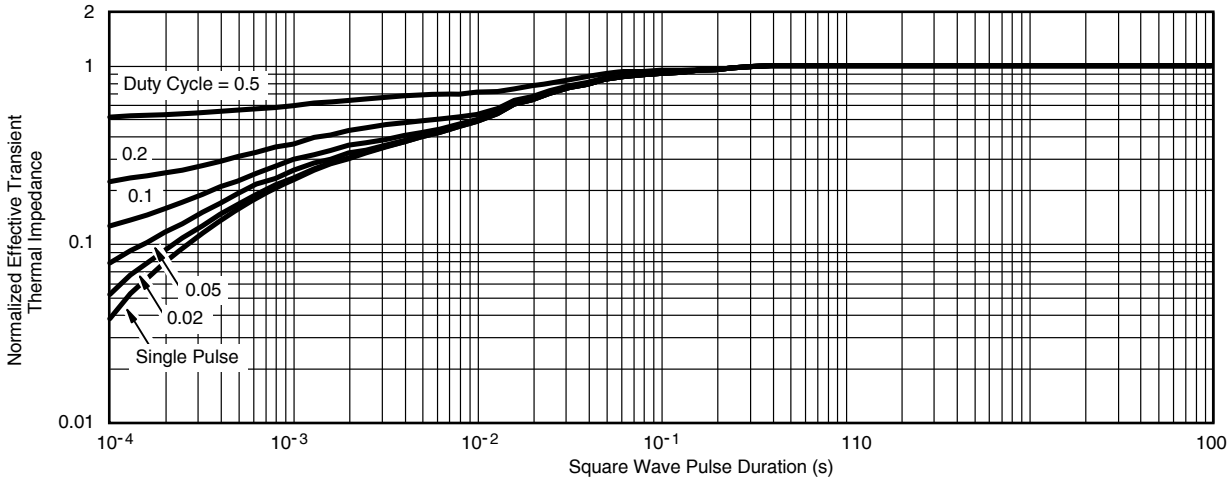
THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case